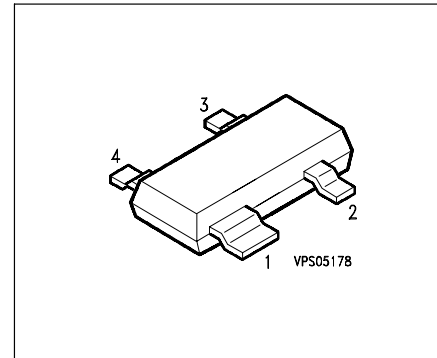


NPN Silicon RF Transistor

- For low-power amplifiers in mobile communication systems (pager) at collector currents from 0.2 to 2.5mA
 $f_T = 7\text{GHz}$
- $F = 2.1\text{dB}$ at 900MHz



ESD: Electrostatic discharge sensitive device, observe handling precaution!

| Type | Marking | Ordering Code | Pin Configuration | | | | Package |
|---------|---------|---------------|-------------------|-------|-------|-------|---------|
| BFP 180 | RDs | Q62702-F1377 | 1 = C | 2 = E | 3 = B | 4 = E | SOT-143 |

Maximum Ratings

| Parameter | Symbol | Values | Unit |
|---|-----------|----------------|------|
| Collector-emitter voltage | V_{CEO} | 8 | V |
| Collector-emitter voltage | V_{CES} | 10 | |
| Collector-base voltage | V_{CBO} | 10 | |
| Emitter-base voltage | V_{EBO} | 2 | |
| Collector current | I_C | 4 | mA |
| Base current | I_B | 0.5 | |
| Total power dissipation $T_S \leq 124\text{ }^\circ\text{C}$ | P_{tot} | 30 | mW |
| Junction temperature | T_j | 150 | |
| Ambient temperature | T_A | - 65 ... + 150 | |
| Storage temperature | T_{stg} | - 65 ... + 150 | |

Thermal Resistance

| | | | |
|--|------------|------------|-----|
| Junction - soldering point ¹⁾ | R_{thJS} | ≤ 875 | K/W |
|--|------------|------------|-----|

1) T_S is measured on the collector lead at the soldering point to the pcb.

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

| Parameter | Symbol | Values | | | Unit |
|--|---------------|--------|------|------|---------------|
| | | min. | typ. | max. | |
| DC Characteristics | | | | | |
| Collector-emitter breakdown voltage $I_C = 1\text{ mA}, I_B = 0$ | $V_{(BR)CEO}$ | 8 | - | - | V |
| Collector-emitter cutoff current $V_{CE} = 10\text{ V}, V_{BE} = 0$ | I_{CES} | - | - | 100 | μA |
| Collector-base cutoff current $V_{CB} = 8\text{ V}, I_E = 0$ | I_{CBO} | - | - | 100 | nA |
| Emitter-base cutoff current $V_{EB} = 1\text{ V}, I_C = 0$ | I_{EBO} | - | - | 1 | μA |
| DC current gain $I_C = 1\text{ mA}, V_{CE} = 5\text{ V}$ | h_{FE} | 30 | 100 | 200 | - |

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

| Parameter | Symbol | Values | | | Unit |
|--|---------------|--------|-------------|------|------|
| | | min. | typ. | max. | |
| AC Characteristics | | | | | |
| Transition frequency $I_C = 3 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $f = 500 \text{ MHz}$ | f_T | 5 | 7 | - | GHz |
| Collector-base capacitance $V_{CB} = 5 \text{ V}$, $V_{BE} = v_{be} = 0$, $f = 1 \text{ MHz}$ | C_{cb} | - | 0.19 | 0.35 | pF |
| Collector-emitter capacitance $V_{CE} = 5 \text{ V}$, $V_{BE} = v_{be} = 0$, $f = 1 \text{ MHz}$ | C_{ce} | - | 0.27 | - | |
| Emitter-base capacitance $V_{EB} = 0.5 \text{ V}$, $V_{CB} = v_{cb} = 0$, $f = 1 \text{ MHz}$ | C_{eb} | - | 0.13 | - | |
| Noise figure $I_C = 1 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $Z_S = Z_{Sopt}$ $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$ | F | - | 2.1 2.25 | - | dB |
| Power gain ¹⁾ $I_C = 1 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $Z_S = Z_{Sopt}$ $Z_L = Z_{Lopt}$ $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$ | G_{ms} | - | 15 12 | - | |
| Transducer gain $I_C = 1 \text{ mA}$, $V_{CE} = 5 \text{ V}$, $Z_S = Z_L = 50 \Omega$ $f = 900 \text{ MHz}$ $f = 1.8 \text{ GHz}$ | $ S_{21e} ^2$ | - | 8.5 7 | - | |

1) $G_{ms} = |S_{21}/S_{12}|$

SPICE Parameters (Gummel-Poon Model, Berkeley-SPICE 2G.6 Syntax) :

Transistor Chip Data

| | | | | | | | | |
|-------|---------|----------|-------|----------|----------|--------|---------|----------|
| IS = | 0.18519 | fA | BF = | 94.687 | - | NF = | 1.0236 | - |
| VAF = | 26.867 | V | IKF = | 0.025252 | A | ISE = | 130.93 | fA |
| NE = | 1.9818 | - | BR = | 20.325 | - | NR = | 0.93013 | - |
| VAR = | 3.2134 | V | IKR = | 0.012138 | A | ISC = | 6.1852 | fA |
| NC = | 1.6195 | - | RB = | 1.4255 | Ω | IRB = | 0.01 | mA |
| RBM = | 60 | Ω | RE = | 3.7045 | Ω | RC = | 0.56 | Ω |
| CJE = | 3.2473 | fF | VJE = | 1.1812 | V | MJE = | 0.41827 | - |
| TF = | 14.866 | ps | XTF = | 0.3062 | - | VTF = | 0.22023 | V |
| ITF = | 1.0202 | mA | PTF = | 0 | deg | CJC = | 183.69 | fF |
| VJC = | 1.1812 | V | MJC = | 0.30423 | - | XCJC = | 0.08334 | - |
| TR = | 2.2648 | ns | CJS = | 0 | fF | VJS = | 0.75 | V |
| MJS = | 0 | - | XTB = | 0 | - | EG = | 1.11 | eV |
| XTI = | 3 | - | FC = | 0.87906 | - | TNOM | 300 | K |

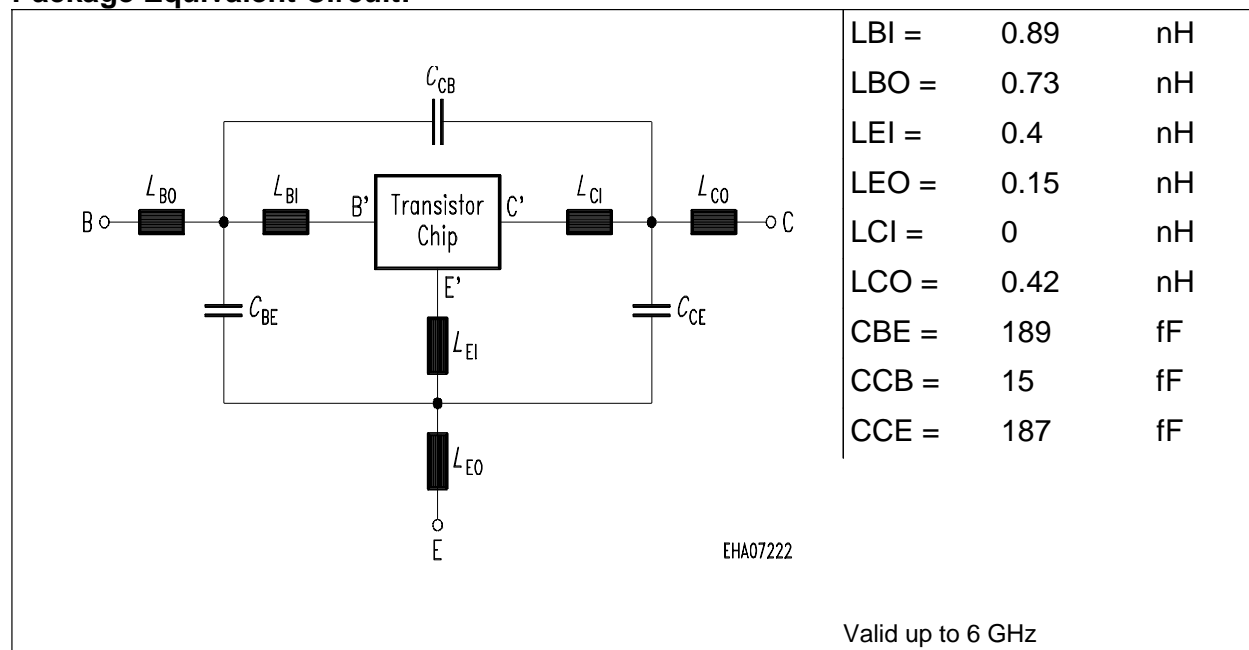
All parameters are ready to use, no scaling is necessary.

Extracted on behalf of SIEMENS Small Signal Semiconductors by:

Institut für Mobil-und Satellitenfunktechnik (IMST)

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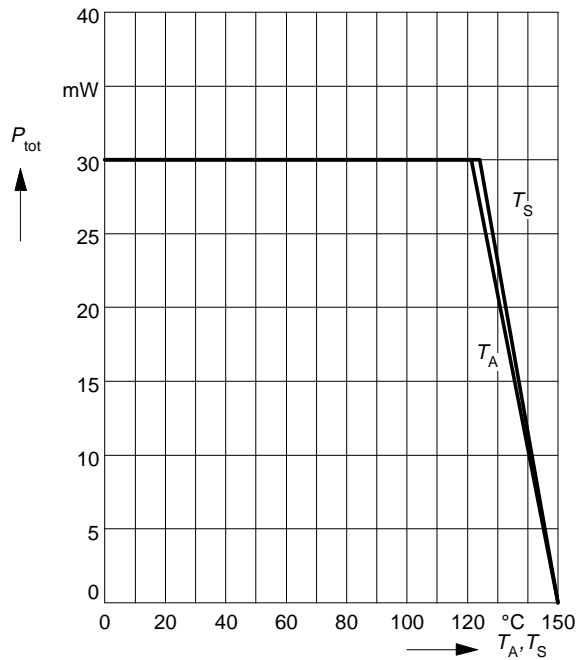
Package Equivalent Circuit:



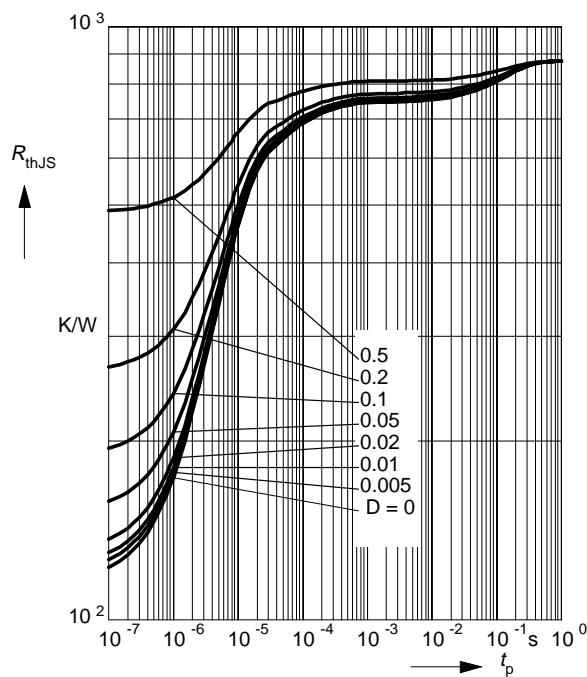
For examples and ready to use parameters please contact your local Siemens distributor or sales office to obtain a Siemens CD-ROM or see Internet: <http://www.siemens.de/Semiconductor/products/35/35.htm>

Total power dissipation $P_{\text{tot}} = f(T_A^*, T_S)$

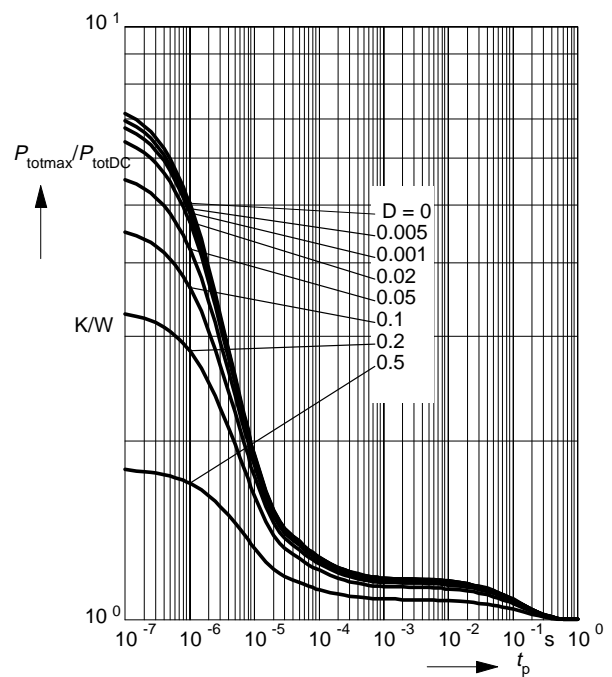
* Package mounted on epoxy



Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$

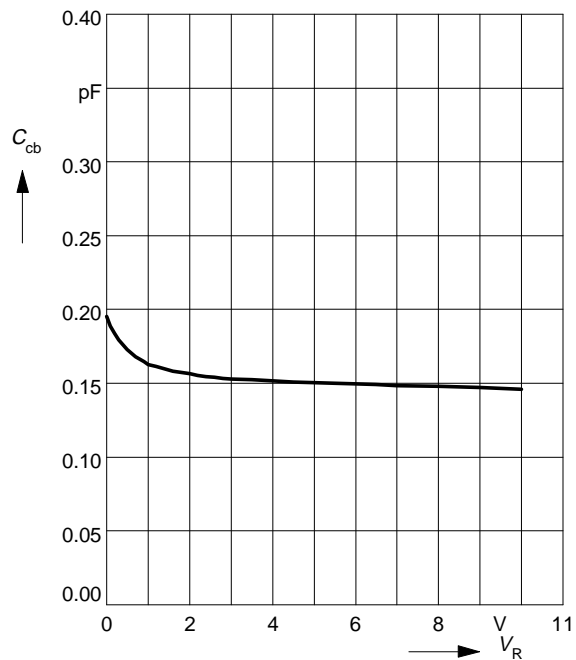


Permissible Pulse Load $P_{\text{totmax}}/P_{\text{totDC}} = f(t_p)$



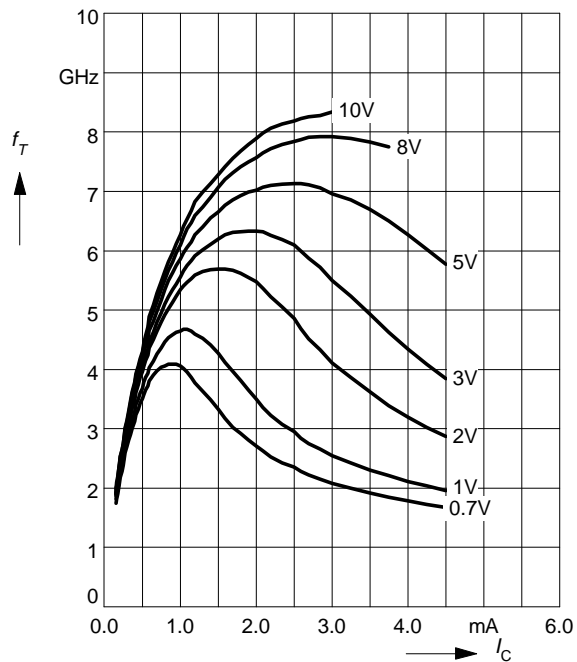
Collector-base capacitance $C_{cb} = f(V_{CB})$

$V_{BE} = v_{be} = 0, f = 1\text{MHz}$



Transition frequency $f_T = f(I_C)$

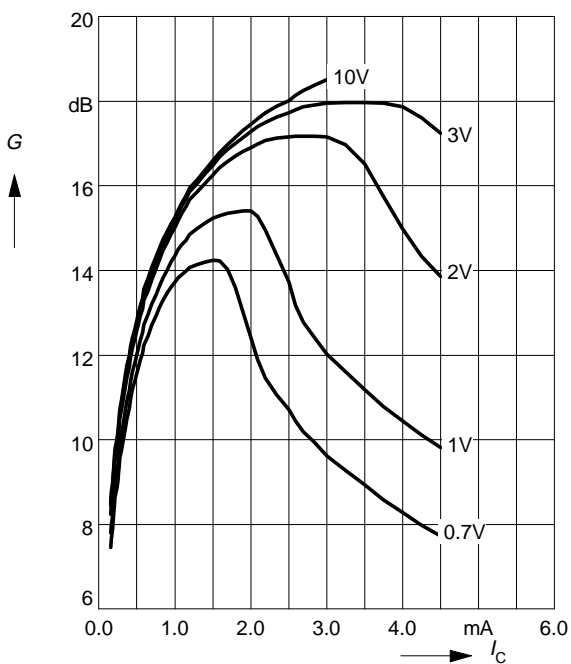
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

$f = 0.9\text{GHz}$

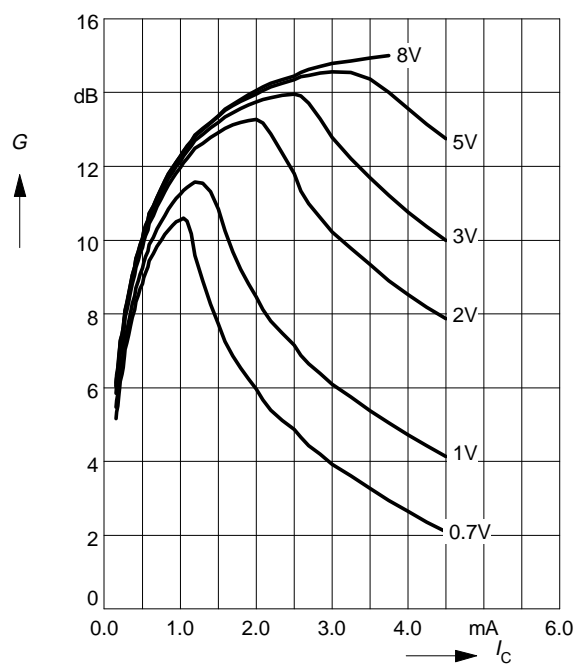
$V_{CE} = \text{Parameter}$



Power Gain $G_{ma}, G_{ms} = f(I_C)$

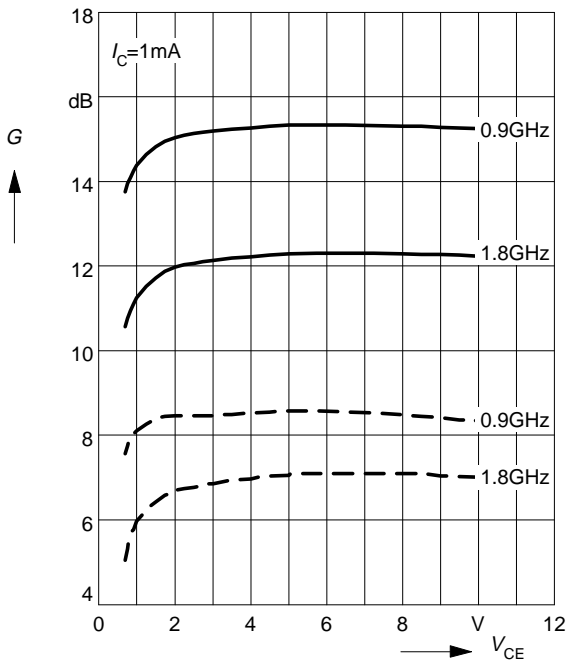
$f = 1.8\text{GHz}$

$V_{CE} = \text{Parameter}$



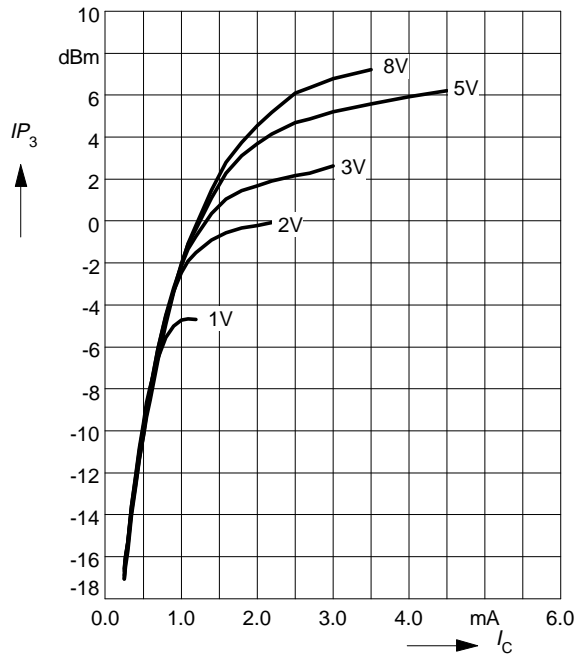
Power Gain $G_{ma}, G_{ms} = f(V_{CE})$: _____
 $|S_{21}|^2 = f(V_{CE})$: - - - - -

$f =$ Parameter



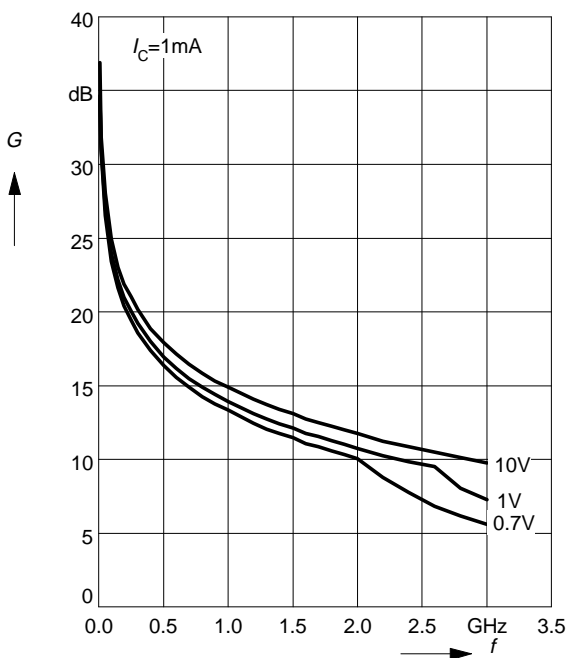
Intermodulation Intercept Point $IP_3 = f(I_C)$
 (3rd order, Output, $Z_S = Z_L = 50\Omega$)

$V_{CE} =$ Parameter, $f = 900\text{MHz}$



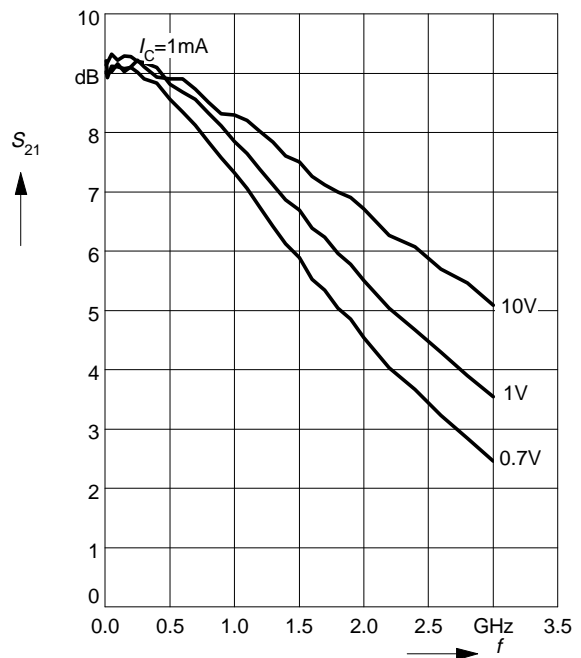
Power Gain $G_{ma}, G_{ms} = f(f)$

$V_{CE} =$ Parameter



Power Gain $|S_{21}|^2 = f(f)$

$V_{CE} =$ Parameter



Package

